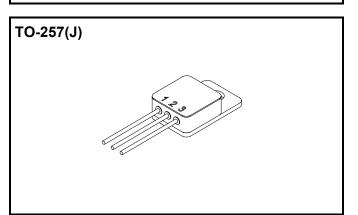


### FEATURES:

- PIV: 100 Volts
- Average Output Current 25 Amps
- Low Reverse Leakage Current
- Low Forward Voltage Drop
- Guard Ring for Overvoltage Protection
- Isolated Hermetically Sealed Package
- Custom Lead Forming Available
- Eutectic Die Attach
- Ultrasonic Aluminum Wire Bonds
- 175°C Operating Junction Temperature
- TX, TXV, and Space Level Screening Available. Consult Factory.

# SSR2010J Series

## 20 AMPS 100 VOLTS SCHOTTKY RECTIFER



MAXIMUM RATINGS <u>1/</u>	Symbol	Value	Unit
Peak Repetitive Reverse Voltage and DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	100	Volts
Average Rectified Forward Current $\frac{2}{}$ (Resistive Load, 60 Hz, Sine Wave, T <sub>A</sub> = 25°C)	lo	20	Amps
<b>Peak Surge Current</b> $\frac{2}{}$ (8.3 ms Pulse, Half Sine Wave, Superimposed on Io, Allow Junction to reach equilibrium between pulses, $T_A = 25^{\circ}C$ )	I <sub>FSM</sub>	300	Amps
Operating and Storage Temperature	T <sub>OP</sub> & T <sub>stg</sub>	-65 to +175	Ĵ
Maximum Thermal Resistance <sup>2/</sup> (Junction to Case)	R <sub>θJC</sub>	1.0	°C/W

#### Available in the Following Configurations:

Rectifier:SSR2010J, SSR2010JDB, and SSR2010JUBCommon Cathode Centertap:SSR2010CTJ, SSR2010CTJDB, and SSR2010CTJUB (See Data Sheet RS0073)Common Anode Centertap:SSR2010CAJ, SSR2010CAJDB, and SSR2010CAJUB (See Data Sheet RS0073)

### NOTE:

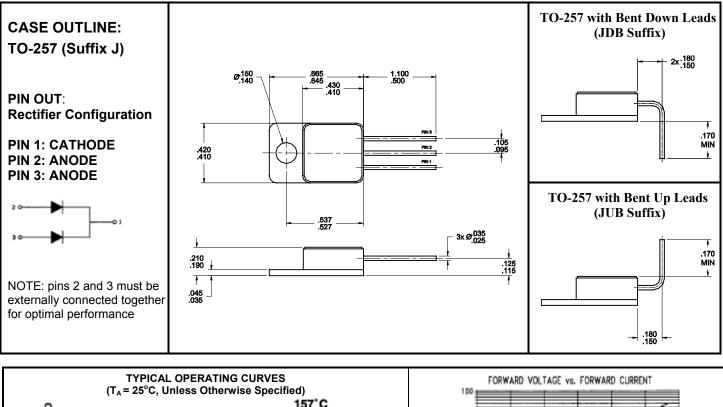
- 1/ at room temperature, unless otherwise specified
- 2/ pins 2 and 3 connected together

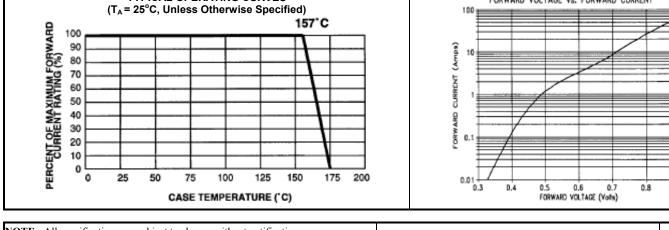
<b>NOTE:</b> All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.	DATA SHEET #: RS0087G	DOC
Seb s for these devices should be reviewed by SSB1 prior to release.	1	

# SSR2010J Series

**Solid State Devices, Inc.** 14701 Firestone Blvd \* La Mirada, Ca 90638 Phone: (562) 404-4474 \* Fax: (562) 404-1773 ssdi@ssdi-power.com \* www.ssdi-power.com

ELECTRICAL CHARACTERISTICS (per leg)		Symbol	Max	Unit
Instantaneous Forward Voltage Drop (T <sub>A</sub> = 25 $^{\circ}$ C, 300 $\mu$ s Pulse)	I <sub>F</sub> = 10 A I <sub>F</sub> = 15 A I <sub>F</sub> = 20 A	V <sub>F1</sub> V <sub>F2</sub> V <sub>F3</sub>	0.8 0.97 1.00	Volts
Instantaneous Forward Voltage Drop ( $T_A = -55^{\circ}C$ , 300 µs Pulse)	I <sub>F</sub> = 10 A	V <sub>F4</sub>	0.93	Volts
Reverse Leakage Current (Rated V <sub>R</sub> , 300 $\mu$ s pulse minimum)	T <sub>A</sub> = 25 <sup>°</sup> C T <sub>C</sub> = 100 <sup>°</sup> C	I <sub>R1</sub> I <sub>R2</sub>	200 10	μA mA
Junction Capacitance ( $V_R = 10 \text{ Vdc}, T_A = 25 \text{ C}, f = 1 \text{MHz}$ )		Сյ	800	pf





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DATA SHEET #: RS0087G

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